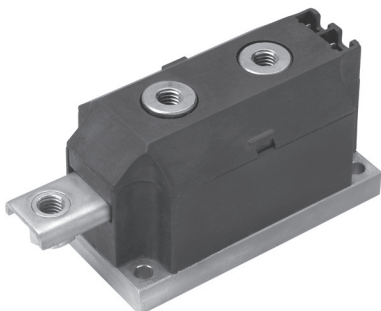


Fast Thyristor/Diode and Thyristor/Thyristor (MAGN-A-PAK Power Modules), 180 A



MAGN-A-PAK

FEATURES

- Fast turn-off thyristor
- Fast recovery diode
- High surge capability
- Electrically isolated baseplate
- 3000 V_{RMS} isolating voltage
- Industrial standard package
- UL approved file E78996 
- Compliant to RoHS directive 2002/95/EC


RoHS
COMPLIANT

PRODUCT SUMMARY

$I_{T(AV)}$	180 A
Type	Modules - Thyristor, Fast

DESCRIPTION

These series of MAGN-A-PAK modules are intended for applications such as self-commutated inverters, DC choppers, electronic welders, induction heating and others where fast switching characteristics are required.

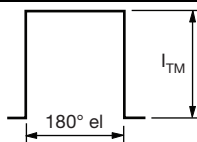
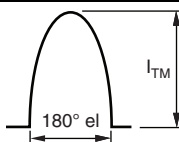
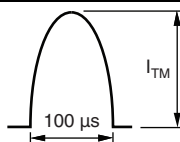
MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{T(AV)}$		180	A
	T_C	85	°C
$I_{T(RMS)}$		400	
I_{TSM}	50 Hz	7130	A
	60 Hz	7470	
I^2t	50 Hz	255	kA ² s
	60 Hz	232	
$I^2\sqrt{t}$		2550	kA ² √s
t_q		20/25	μs
t_{rr}		2	
V_{DRM}/V_{RRM}		800/1200	V
T_J	Range	- 40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	V_{RRM}/V_{DRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM}/I_{DRM} MAXIMUM AT $T_J = 125\text{ °C}$ mA
VSK.F180-	08	800	800	50
	12	1200	1200	

CURRENT CARRYING CAPABILITY							
FREQUENCY							UNITS
50 Hz	370	530	565	800	2400	3150	A
400 Hz	435	650	670	1000	1540	2050	
2500 Hz	290	430	490	720	610	830	
5000 Hz	240	345	390	540	390	540	
10 000 Hz	170	270	290	390	-	-	
Recovery voltage V_r	50		50		50		V
Voltage before turn-on V_d	80 % V_{DRM}		80 % V_{DRM}		80 % V_{DRM}		
Rise of on-state current di/dt	50		-		-		A/μs
Case temperature	85	60	85	60	85	60	°C
Equivalent values for RC circuit	10/0.47		10/0.47		10/0.47		Ω/μF

ON-STATE CONDUCTION					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current at case temperature	$I_{T(AV)}$	180° conduction, half sine wave		180	A
				85	°C
Maximum RMS current	$I_{T(RMS)}$	As AC switch		400	A
Maximum peak, one-cycle non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reapplied	7130	
		t = 8.3 ms	No voltage reapplied	7470	
		t = 10 ms	100 % V_{RRM} reapplied	6000	
		t = 8.3 ms	100 % V_{RRM} reapplied	6280	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied	255	kA ² s
		t = 8.3 ms	No voltage reapplied	232	
		t = 10 ms	100 % V_{RRM} reapplied	180	
		t = 8.3 ms	100 % V_{RRM} reapplied	164	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 ms to 10 ms, no voltage reapplied		2550	kA ² √s
Low level value or threshold voltage	$V_{T(TO)1}$	(16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$), $T_J = T_J$ maximum		1.30	V
High level value of threshold voltage	$V_{T(TO)2}$	(I > $\pi \times I_{T(AV)}$), $T_J = T_J$ maximum		1.38	
Low level value on-state slope resistance	r_{t1}	(16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$), $T_J = T_J$ maximum		0.90	mΩ
High level value on-state slope resistance	r_{t2}	(I > $\pi \times I_{T(AV)}$), $T_J = T_J$ maximum		0.71	
Maximum on-state voltage drop	V_{TM}	$I_{pk} = 600$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sine pulse		1.84	V
Maximum holding current	I_H	$T_J = 25$ °C, $I_T > 30$ A		600	mA
Typical latching current	I_L	$T_J = 25$ °C, $V_A = 12$ V, $R_a = 6$ Ω, $I_g = 1$ A		1000	



Vishay Semiconductors

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
			K	J	
Maximum non-repetitive rate of rise	di/dt	Gate drive 20 V, 20 Ω , $t_r \leq 1$ ms, $V_D = 80\%$ V_{DRM} $T_J = 25^\circ\text{C}$	800		A/ μs
Maximum recovery time	t_{rr}	$I_{TM} = 350$ A, $di/dt = -25$ A/ μs , $V_R = 50$ V, $T_J = 25^\circ\text{C}$	2		μs
Maximum turn-off time	t_q	$I_{TM} = 750$ A; $T_J = 125^\circ\text{C}$; $di/dt = -25$ A/ μs ; $V_R = 50$ V; $dV/dt = 400$ V/ μs linear to 80% V_{DRM}	20	25	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = 125 °C, exponential to 67 % V _{DRM}	1000	V/μs
RMS insulation voltage	V _{INS}	50 Hz, circuit to base, all terminals shorted, 25 °C, 1 s	3000	V
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	T _J = 125 °C, rated V _{DRM} /V _{RRM} applied	50	mA

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}	$f = 50 \text{ Hz}$, $d\% = 50$	60	W
Maximum peak average gate power	$P_{G(AV)}$	$T_J = 125 \text{ }^{\circ}\text{C}$, $f = 50 \text{ Hz}$, $d\% = 50$	10	
Maximum peak positive gate current	I_{GM}	$T_J = 125 \text{ }^{\circ}\text{C}$, $t_p \leq 5 \text{ ms}$	10	A
Maximum peak negative gate voltage	$-V_{GM}$		5	V
Maximum DC gate current required to trigger	I_{GT}	$T_J = 25 \text{ }^{\circ}\text{C}$, $V_{ak} 12 \text{ V}$, $R_a = 6 \text{ }\Omega$	200	mA
DC gate voltage required to trigger	V_{GT}		3	V
DC gate current not to trigger	I_{GD}	$T_J = 125 \text{ }^{\circ}\text{C}$, rated V_{DRM} applied	20	mA
DC gate voltage not to trigger	V_{GD}		0.25	V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating temperature range	T_J		- 40 to 125	°C
Maximum storage temperature range	T_{Stg}		- 40 to 150	
Maximum thermal resistance, junction to case per junction	R_{thJC}	DC operation	0.125	K/W
Maximum thermal resistance, case to heatsink per module	R_{thCS}	Mounting surface, flat and greased	0.02	
Mounting torque $\pm 10\%$	MAP to heatsink busbar to MAP	A mounting compound is recommended. The torque should be rechecked after a period of 3 hours to allow for the spread of the compound. Use of cable lugs is not recommended, busbar should be used and restrained during tightening. Threads must be lubricated with a compound.	4 to 6 (35 to 53)	N · m (lbf · in)
Approximate weight			500	g
			17.8	oz.
Case style			MAGN-A-PAK	

ΔR_{thJC} CONDUCTION				
CONDUCTIONS ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.009	0.006	$T_J = 125^\circ\text{C}$	K/W
120°	0.010	0.011		
90°	0.014	0.015		
60°	0.020	0.020		
30°	0.032	0.033		

Note

- Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

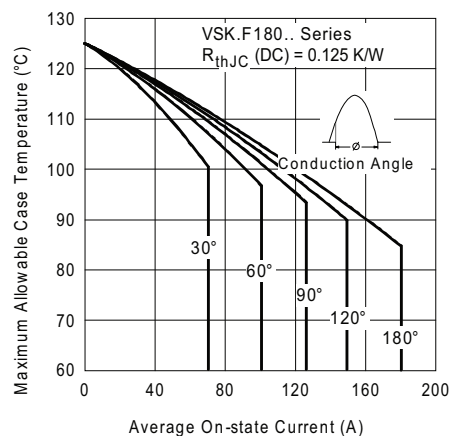


Fig. 1 - Current Ratings Characteristics

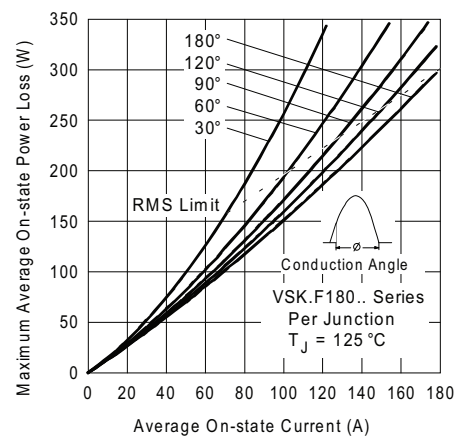


Fig. 3 - On-State Power Loss Characteristics

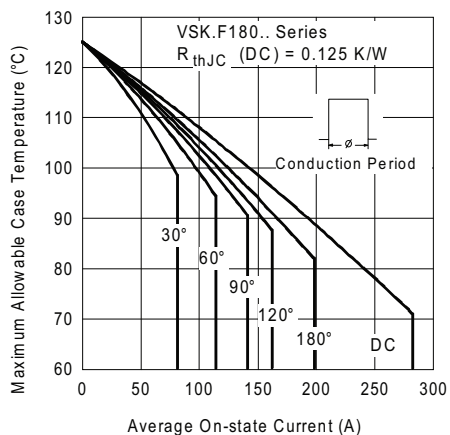


Fig. 2 - Current Ratings Characteristics

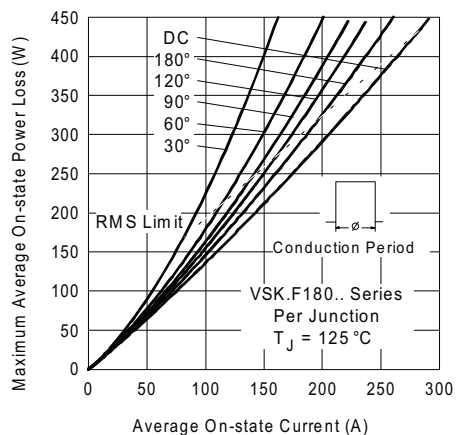


Fig. 4 - On-State Power Loss Characteristics

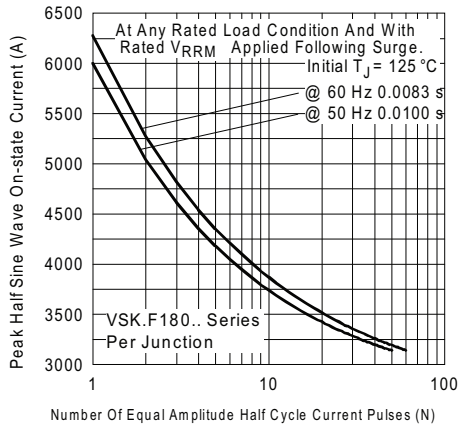


Fig. 5 - Maximum Non-Repetitive Surge Current

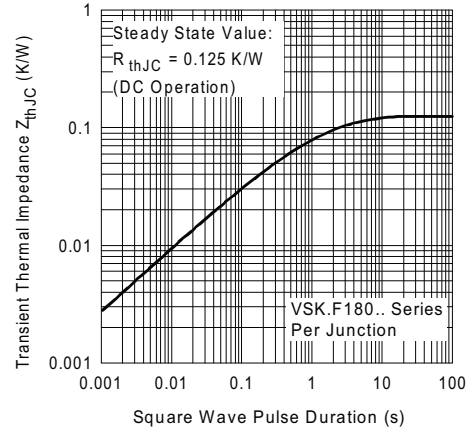


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

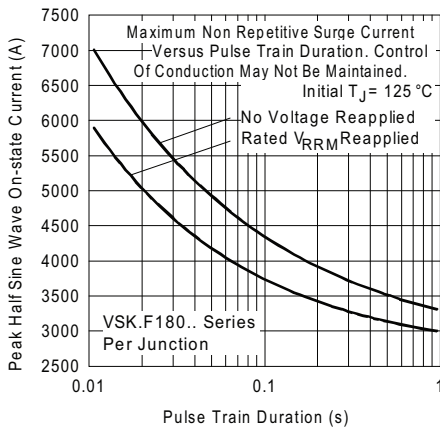


Fig. 6 - Maximum Non-Repetitive Surge Current

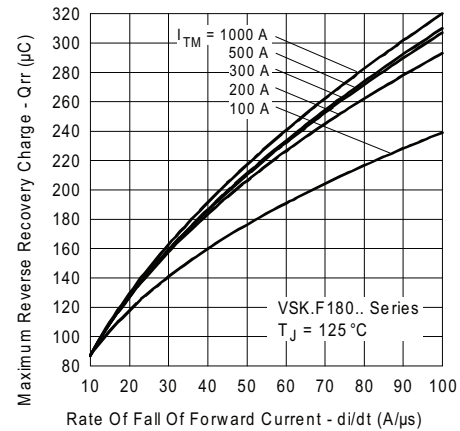


Fig. 9 - Reverse Recovery Charge Characteristics

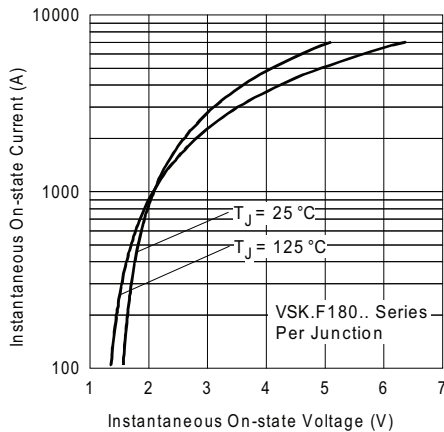


Fig. 7 - On-State Voltage Drop Characteristics

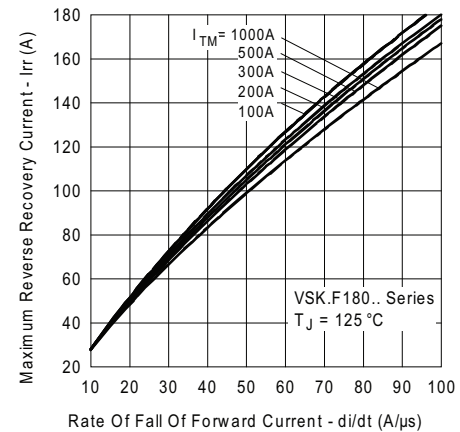


Fig. 10 - Reverse Recovery Current Characteristics

VSK.F180..P Series

Vishay Semiconductors Fast Thyristor/Diode and Thyristor/Thyristor
(MAGN-A-PAK Power Modules), 180 A

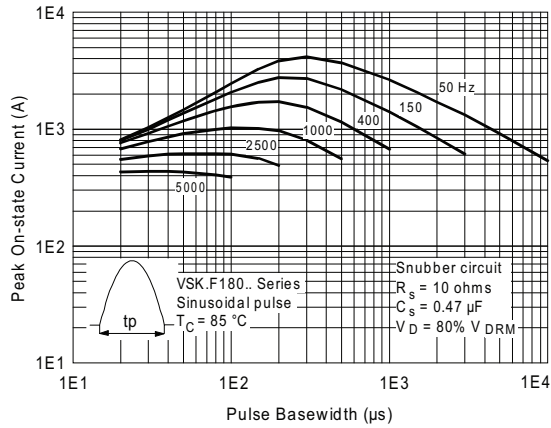


Fig. 11 - Frequency Characteristics

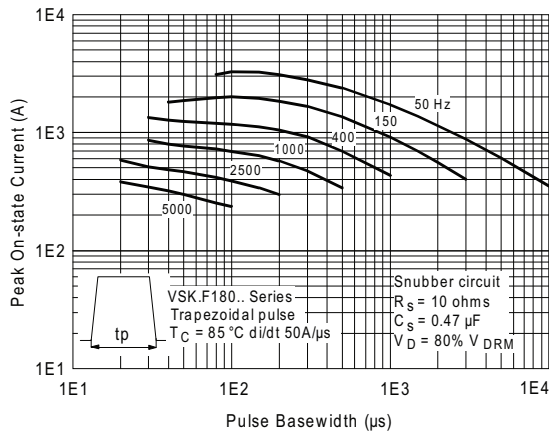
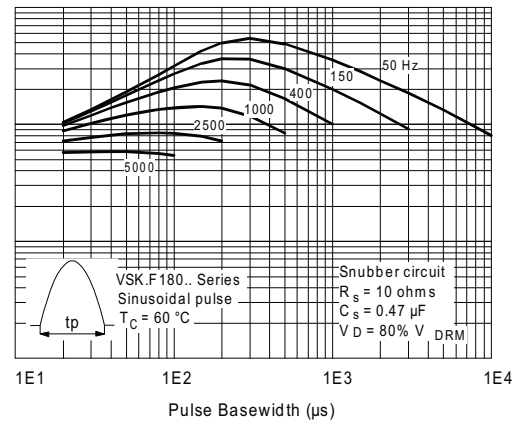


Fig. 12 - Frequency Characteristics

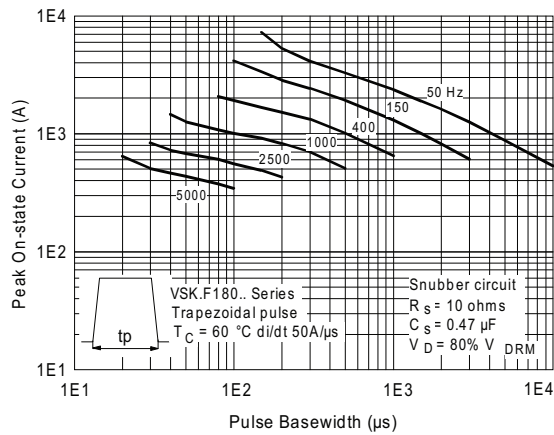
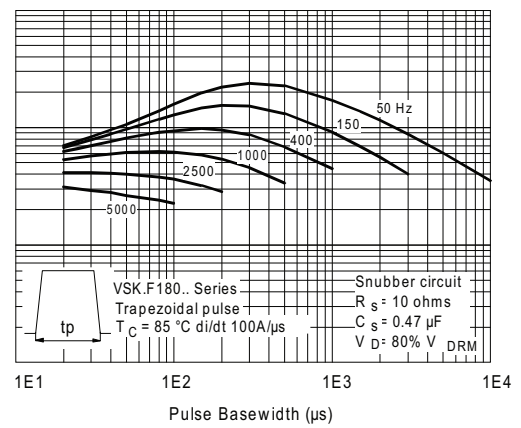
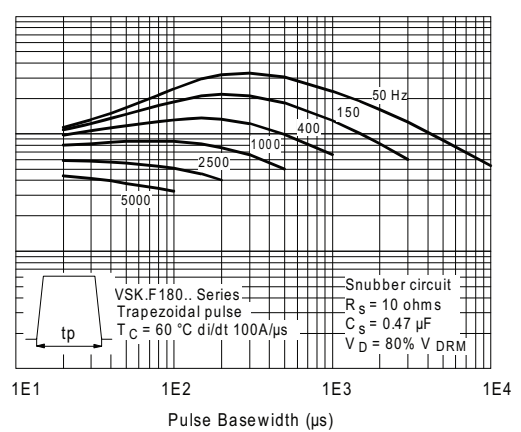


Fig. 13 - Frequency Characteristics



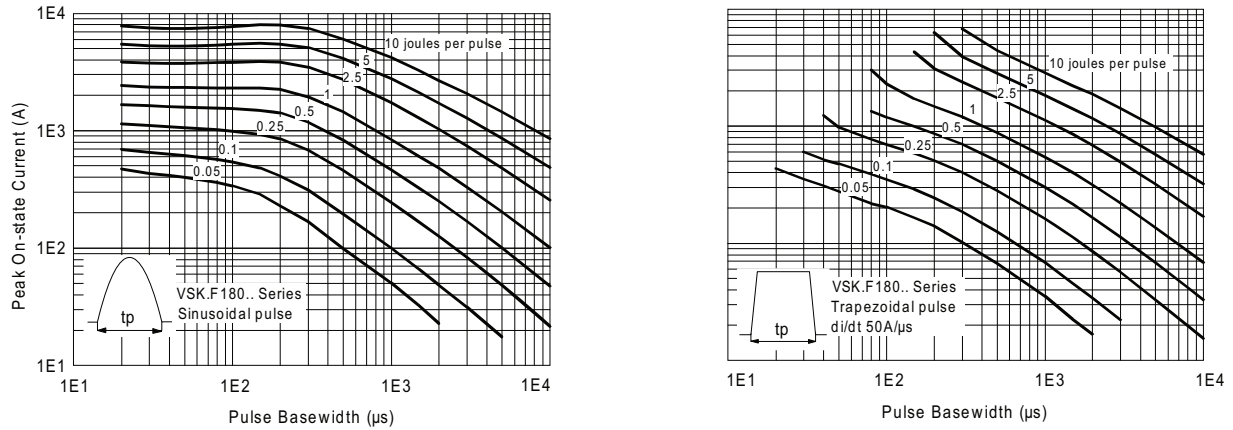


Fig. 14 - Maximum On-State Energy Power Loss Characteristics

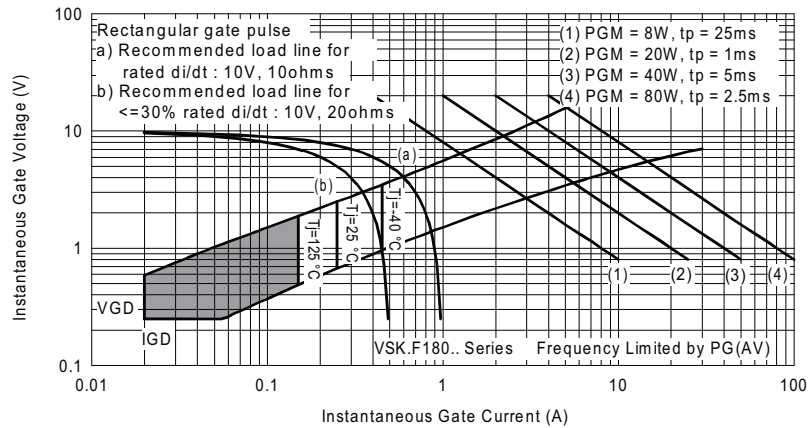


Fig. 15 - Gate Characteristics

Vishay Semiconductors Fast Thyristor/Diode and Thyristor/Thyristor
(MAGN-A-PAK Power Modules), 180 A



Device code

VSK	T	F	180	-	12	H	K	P
1	2	3	4	5	6	7	8	

- | | | |
|----------|---|---|
| 1 | - | Module type |
| 2 | - | Circuit configuration (see circuit configuration table) |
| 3 | - | Fast SCR |
| 4 | - | Current rating: $I_{T(AV)} \times 10$ rounded |
| 5 | - | Voltage code $\times 100 = V_{RRM}$ (see Voltage Ratings table) |
| 6 | - | dV/dt code: $H \leq 400 \text{ V}/\mu\text{s}$ |
| 7 | - | t_q code: $K \leq 20 \mu\text{s}$
$J \leq 25 \mu\text{s}$ |
| 8 | - | P = Lead (Pb)-free |

- To order the optional hardware go to www.vishay.com/doc?95172

CIRCUIT CONFIGURATION		
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Two SCRs common cathodes	U	VSKUF..
SCR/diode common cathodes	K	VSKKF..
Two SCRs common anodes	V	VSKVF..

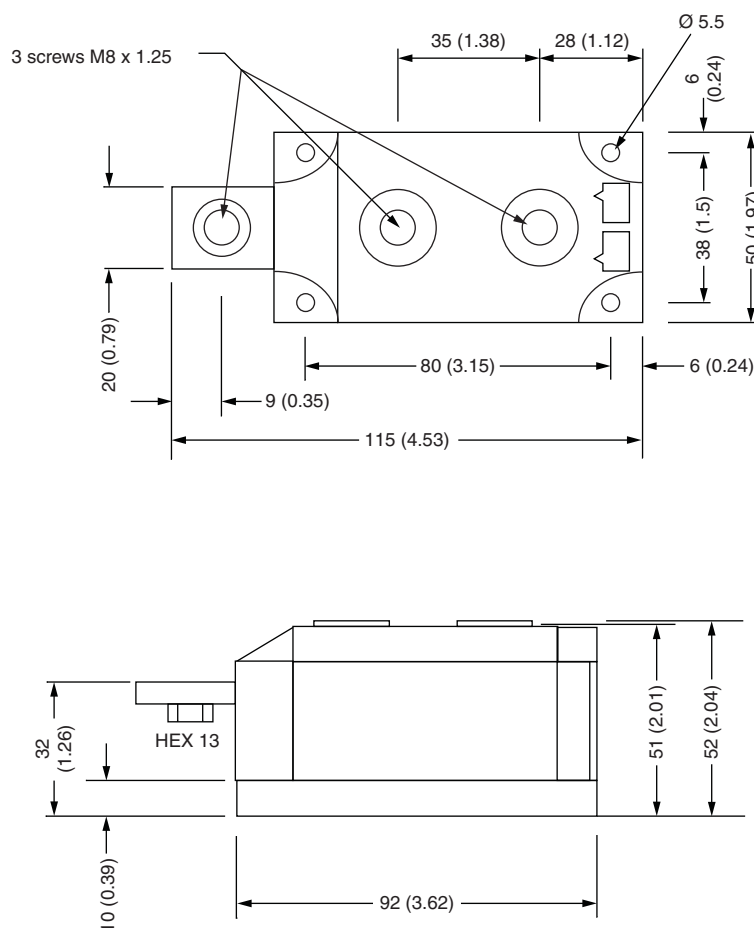


CIRCUIT CONFIGURATION		
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
SCR/diode common anodes	N	
SCR/diode doubler circuit, negative control	L	
Two SCRs doubler circuit	T	
SCR/diode doubler circuit, positive control	H	

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95086

MAGN-A-PAK

DIMENSIONS in millimeters (inches)



Notes

- Dimensions are nominal
- Full engineering drawings are available on request
- UL identification number for gate and cathode wire: UL 1385
- UL identification number for package: UL 94 V-0



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishay or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.



**Стандарт
Электрон
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331